## **BC549C, BC550C**

## **Low Noise Transistors**

#### **NPN Silicon**

#### **Features**

• These are Pb-Free Devices\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage  BC549C BC550C	V <sub>CEO</sub>	30 45	Vdc
Collector – Base Voltage  BC549C BC550C	V <sub>CBO</sub>	30 50	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current – Continuous	Ic	100	Vdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above = 25°C	P <sub>D</sub>	625 5.0	mW mW/°C
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above = 25°C	P <sub>D</sub>	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

#### THERMAL CHARACTERISTICS

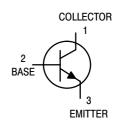
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



#### ON Semiconductor®

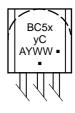
#### http://onsemi.com





TO-92 CASE 29 STYLE 17

#### MARKING DIAGRAM



BC5xyC = Device Code x = 4 or 5

y = 9 or 0

A = Assembly Location

Y = Year
WW = Work Week
Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping
BC549CG	TO-92 (Pb-Free)	5000 Units / Bulk
BC550CG	TO-92 (Pb-Free)	5000 Units / Bulk

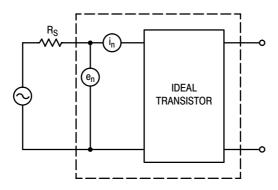
<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### BC549C, BC550C

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	45	-	_	Vdc
Collector – Base Breakdown Voltage $(I_C = 10 \mu Adc, I_E = 0)$	V <sub>(BR)CBO</sub>	50	-	-	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 10 \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	5.0	-	-	Vdc
Collector Cutoff Current	I <sub>CBO</sub>	_ _	- -	15 5.0	nAdc μAdc
Emitter Cutoff Current $(V_{EB} = 4.0 \text{ Vdc}, I_C = 0)$	I <sub>EBO</sub>	-	-	15	nAdc
ON CHARACTERISTICS					
DC Current Gain	h <sub>FE</sub>	100 420	270 500	_ 800	-
Collector – Emitter Saturation Voltage	V <sub>CE(sat)</sub>	- - -	0.075 0.3 0.25	0.25 0.6 0.6	Vdc
Base–Emitter Saturation Voltage $(I_C = 100 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$	V <sub>BE(sat)</sub>	-	1.1	-	Vdc
Base–Emitter On Voltage $ \begin{aligned} &(I_C=10~\mu\text{Adc},~V_{CE}=5.0~\text{Vdc})\\ &(I_C=100~\mu\text{Adc},~V_{CE}=5.0~\text{Vdc})\\ &(I_C=2.0~\text{mAdc},~V_{CE}=5.0~\text{Vdc}) \end{aligned} $	V <sub>BE(on)</sub>	- - 0.55	0.52 0.55 0.62	- - 0.7	Vdc
SMALL-SIGNAL CHARACTERISTICS	·				
Current – Gain — Bandwidth Product (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 100 MHz)	f <sub>T</sub>	-	250	-	MHz
Collector–Base Capacitance $(V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	C <sub>cbo</sub>	_	2.5	_	pF
Small–Signal Current Gain ( $I_C = 2.0 \text{ mAdc}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$ )	h <sub>fe</sub>	450	600	900	-
Noise Figure $ \begin{array}{l} \text{(I}_{C} = 200 \; \mu\text{Adc, V}_{CE} = 5.0 \; \text{Vdc, R}_{S} = 2.0 \; \text{k}\Omega,  \text{f} = 1.0 \; \text{kHz)} \\ \text{(I}_{C} = 200 \; \mu\text{Adc, V}_{CE} = 5.0 \; \text{Vdc, R}_{S} = 100 \; \text{k}\Omega,  \text{f} = 1.0 \; \text{kHz)} \end{array} $	NF <sub>1</sub> NF <sub>2</sub>	_ _	0.6	2.5 10	dB

I<sub>B</sub> is value for which I<sub>C</sub> = 11 mA at V<sub>CE</sub> = 1.0 V.
 Pulse test = 300 μs – Duty cycle = 2%.



**Figure 1. Transistor Noise Model** 

### BC549C, BC550C

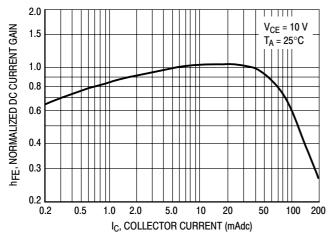


Figure 2. Normalized DC Current Gain

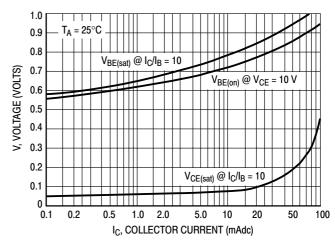


Figure 3. "Saturation" and "On" Voltages

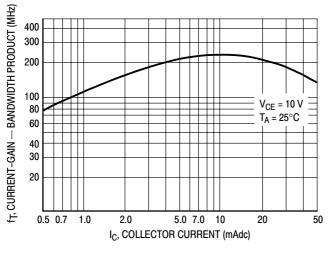


Figure 4. Current-Gain — Bandwidth Product

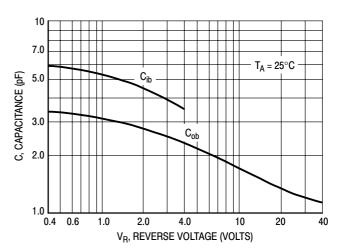


Figure 5. Capacitance

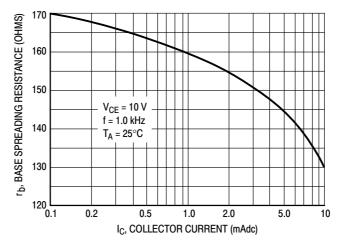
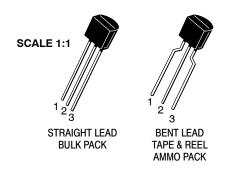
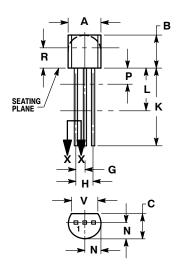


Figure 6. Base Spreading Resistance



**TO-92 (TO-226)** CASE 29-11 **ISSUE AM** 

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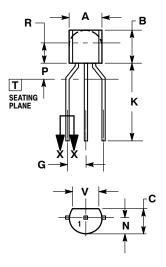


STRAIGHT LEAD **BULK PACK** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
v	0.135		3 43	



**BENT LEAD** TAPE & REEL AMMO PACK



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS				
DIM	MIN	MAX			
Α	4.45	5.20			
В	4.32	5.33			
С	3.18	4.19			
D	0.40	0.54			
G	2.40	2.80			
J	0.39	0.50			
K	12.70				
N	2.04	2.66			
P	1.50	4.00			
R	2.93				
V	3.43				

#### **STYLES ON PAGE 2**

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# ISSUE AM

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STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	STYLE 4: PIN 1. 2. 3.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	DRAIN SOURCE GATE
STYLE 6: PIN 1. 2. 3.	GATE SOURCE & SUBSTRATE DRAIN	STYLE 7: PIN 1. 2. 3.	SOURCE DRAIN GATE	STYLE 8: PIN 1. 2. 3.	DRAIN GATE SOURCE & SUBSTRATE	STYLE 9: PIN 1. 2. 3.	BASE 1 EMITTER BASE 2	STYLE 10: PIN 1. 2. 3.	CATHODE GATE
STYLE 11: PIN 1. 2. 3.	ANODE CATHODE & ANODE CATHODE	STYLE 12: PIN 1. 2. 3.	MAIN TERMINAL 1 GATE MAIN TERMINAL 2	STYLE 13: PIN 1. 2. 3.	ANODE 1 GATE CATHODE 2	STYLE 14: PIN 1. 2. 3.	EMITTER COLLECTOR BASE	PIN 1. 2.	
2.	ANODE GATE CATHODE	2.	BASE	2.	ANODE CATHODE NOT CONNECTED	2.	ANODE	2.	NOT CONNECTED
PIN 1. 2.	COLLECTOR	PIN 1. 2.	SOURCE GATE DRAIN	STYLE 23: PIN 1. 2. 3.	GATE SOURCE DRAIN	STYLE 24: PIN 1. 2. 3.	EMITTER COLLECTOR/ANODE CATHODE		MT 1 GATE
		2.	MT SUBSTRATE MT	2.		PIN 1. 2.	ANODE	STYLE 30: PIN 1. 2. 3.	DRAIN GATE
	GATE	PIN 1. 2.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN	2.			

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